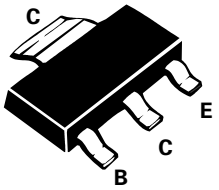
SOT223 PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

ISSUE 3 - NOVEMBER 1995 ✪

FZT593

COMPLEMENTARY TO FZT493
PARTMARKING DETAIL - FZT593



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-120	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-2	A
Continuous Collector Current	I_C	-1	A
Base Current	I_B	-200	mA
Power Dissipation at T_{amb}=25°C	P_{tot}	2	W
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Breakdown Voltages	$V_{(BR)CBO}$	-120		V	I_C=-100μA
	$V_{(BR)CEO}$	-100		V	I_C=-10mA*
	$V_{(BR)EBO}$	-5		V	I_E=-100μA
Collector Cut-Off Current	I_{CBO}		-100	nA	V_{CB}=-100V
Emitter Cut-Off Current	I_{EBO}		-100	nA	V_{EB}=-4V
Collector-Emitter Cut-Off Current	I_{CES}		-100	nA	V_{CES}=-100V
Saturation Voltages	$V_{CE(sat)}$		-0.2 -0.3	V V	I_C=-250mA,I_B=-25mA* I_C=-500mA I_B=-50mA*
	$V_{BE(sat)}$		-1.1	V	I_C=-500mA,I_B=-50mA*
Base-Emitter Turn-on Voltage	$V_{BE(on)}$		-1.0	V	I_C=-1mA, V_{CE}=-5V*
Static Forward Current Transfer Ratio	h_{FE}	100 100 100 50	 300		I_C=-1mA, V_{CE}=-5V I_C=-250mA,V_{CE}=-5V* I_C=-500mA, V_{CE}=-5V* I_C=-1A, V_{CE}=-5V*
Transition Frequency	f_T	50		MHz	I_C=-50mA, V_{CE}=-10V f=100MHz
Output Capacitance	C_{obo}		5	pF	V_{CB}=-10V, f=1MHz

*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤ 2%
For typical Characteristics graphs see FMMT593 datasheet

littlediode
COMPONENTS FOR ALL

Littlediode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

LittleDiode.com

Looking forward to providing you with the best possible service.